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November 2013

FDP039N08B

N-Channel PowerTrench[®] MOSFET 80 V, 171 A, 3.9 m Ω

Features

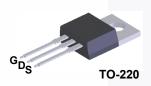
- $R_{DS(on)}$ = 3.16 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 100 A
- Low FOM R_{DS(on)} * Q_G
- Low Reverse-Recovery Charge, Q_{rr} = 87.9 nC
- · Soft Reverse-Recovery Body Diode
- Enables High Efficiency in Synchronous Rectification
- · Fast Switching Speed
- · 100% UIL Tested
- · RoHS Compliant

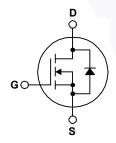
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	Parameter		
V _{DSS}	Drain to Source Voltage			80	V
V_{GSS}	Gate to Source Voltage			±20	V
		- Continuous (T _C = 25°C	C, Silicon Limited)	171*	
I _D	I _D Drain Current		C, Silicon Limited)	121*	Α
		- Continuous (T _C = 25°C	- Continuous (T _C = 25°C, Package Limited)		
I _{DM}	Drain Current	- Pulsed	(Note 1)	684	Α
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2)	547	mJ
dv/dt	Peak Diode Recovery dv	/dt	(Note 3)	6.0	V/ns
D	Dower Dissipation	$(T_C = 25^{\circ}C)$		214	W
P_{D}	Power Dissipation	- Derate Above 25°C		1.43	W/°C
T _J , T _{STG}	Operating and Storage T	emperature Range		-55 to +175	οС
TL	Maximum Lead Tempera	ture for Soldering, 1/8" from Case	for 5 Seconds	300	°C

^{*} Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter FDP039N08B_F10			
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.7	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	*0/00	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP039N08B_F102	FDP039N08B	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{V}$	80	-	-	V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.089	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 64 V, V _{GS} = 0 V	-	-	1	μА
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 64 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 100 A	1	3.16	3.9	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 100 A	1	180	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 40.V. V 0.V	-	7105	9450	pF
C _{oss}	Output Capacitance	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	-	1110	1475	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12	-	30	-	pF
C _{oss(er)}	Energy Related Output Capacitance	V _{DS} = 40 V, V _{GS} = 0 V	-	1656	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V		-	102	133	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 40 \text{ V}, I_{D} = 100 \text{ A},$	-	39.9	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	V _{GS} = 10 V	-	22	-	nC
V _{plateau}	Gate Plateau Volatge	(Note 4)	-	5.6	-	V
Q _{sync}	Total Gate Charge Sync.	V _{DS} = 0 V, I _D = 50 A	-	87.4	-	nC
Q _{oss}	Output Charge	V _{DS} = 40 V, V _{GS} = 0 V	-	99.2	-	nC

Switching Characteristics

•						
t _{d(on)}	Turn-On Delay Time		-/	36	82	ns
t _r	Turn-On Rise Time	V _{DD} = 40 V, I _D = 100 A,	-	49	108	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_{G} = 4.7 Ω	/ -	71	152	ns
t _f	Turn-Off Fall Time	(Note 4)	-	29	68	ns
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	2.2	-	Ω

Drain-Source Diode Characteristics

L	Maximum Continuous Drain to Source Diode Ford	Maximum Continuous Drain to Source Diode Forward Current			171*	Δ
IS	Maximum Continuous Drain to Source Diode For	ward Current		_	17.1	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	684	Α
V_{SD}	Drain to Source Diode Forward Voltage V _{GS}	_s = 0 V, I _{SD} = 100 A	-	-	1.3	V
t _{rr}	Reverse Recovery Time V _{GS}	$_{S} = 0 \text{ V}, \text{ V}_{DD} = 40 \text{ V}, \text{ I}_{SD} = 100 \text{ A},$	-	70.1	-	ns
Q_{rr}	Reverse Recovery Charge dI _F /c	dt = 100 A/μs	-	87.9	-	nC

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 3 mH, I_{AS} = 19.1 A, starting T_J = 25°C.
- 3. I_{SD} \leq 100 A, di/dt \leq 200 A/ μ s, V_DD \leq BV_DSS, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

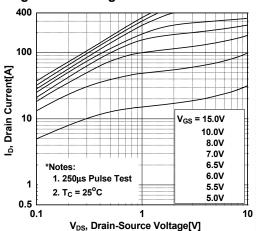


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

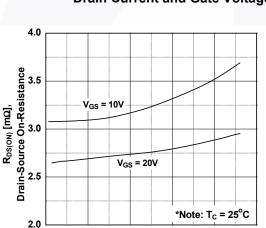


Figure 5. Capacitance Characteristics

200

ID, Drain Current [A]

300

400

500

100

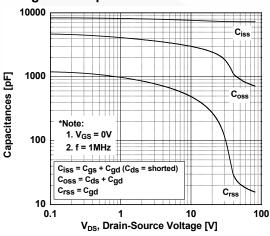


Figure 2. Transfer Characteristics

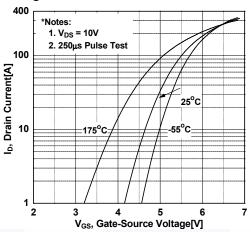


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

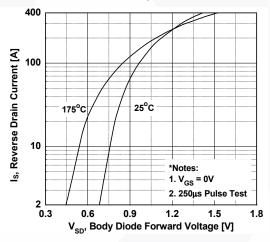
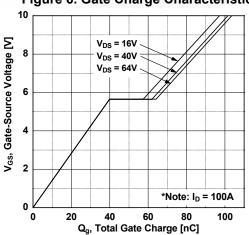


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

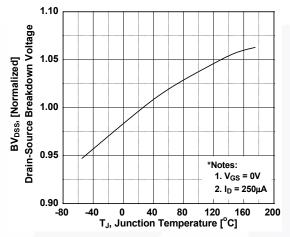


Figure 9. Maximum Safe Operating Area

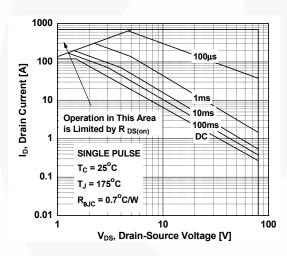


Figure 11. Eoss vs. Drain to Source Voltage

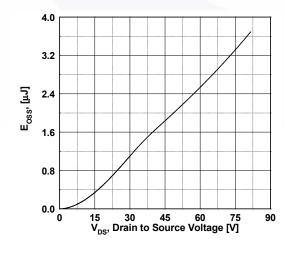


Figure 8. On-Resistance Variation vs. Temperature

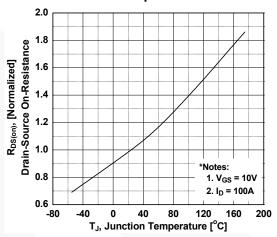


Figure 10. Maximum Drain Current vs. Case Temperature

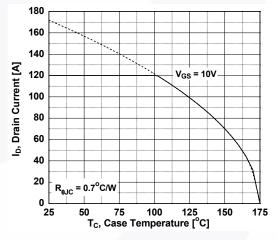
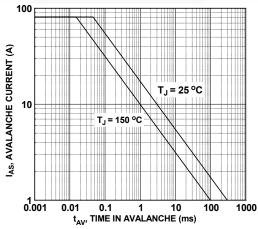
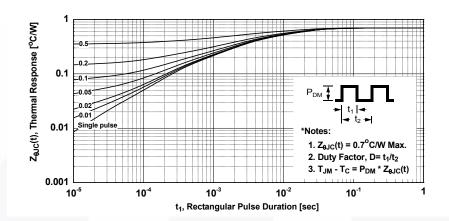


Figure 12. Unclamped Inductive Switching Capability



Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve



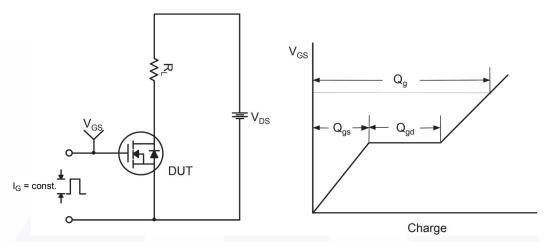


Figure 14. Gate Charge Test Circuit & Waveform



Figure 15. Resistive Switching Test Circuit & Waveforms

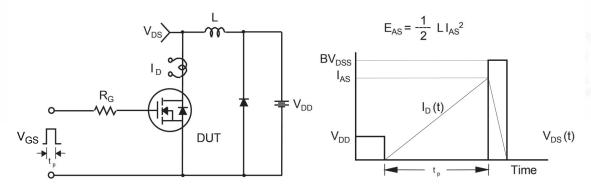


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

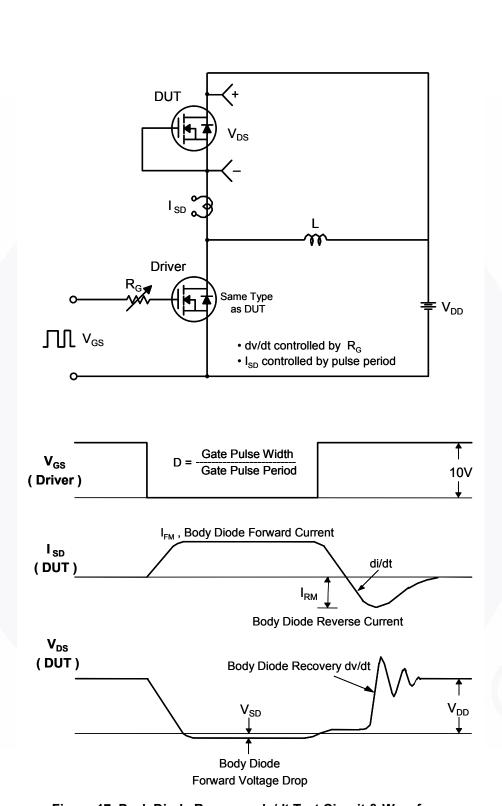


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

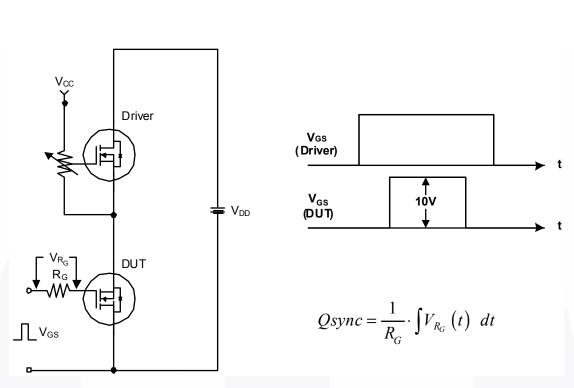


Figure 18. Total Gate Charge Qsync. Test Circuit & Waveforms

Mechanical Dimensions

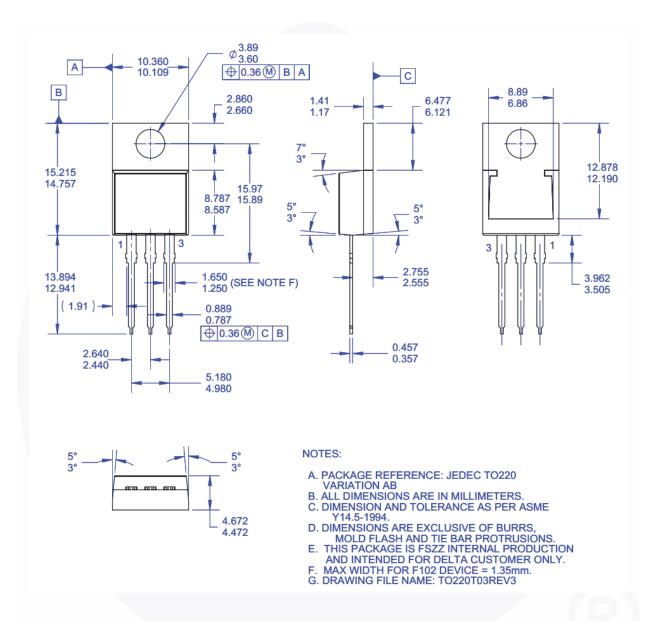


Figure 19. TO-220, Molded, 3-Lead, Jedec Variation AB (Delta)

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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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